

SB5560S 55A SOTs

FEATURES

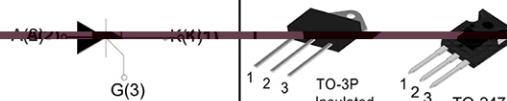
- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Parameters Summary

VD/VR:1200/1600V IT(RMS):55A IGT :60mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	value	Unit
Storage junction temperature range	T _{stg}	-40~150	°C
Operating junction temperature range	T _j	-40~125	°C
Repetitive peak off-state voltage (T=25°C)	V _{DRM}	1200/1600	V
Repetitive peak reverse voltage (T=25°C)	V _{RPM}	1200/1600	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RPM} +100	V
RMS on-state current	I _{TSM}	55	A
TO-3PIs.(TC=80°C)			
TO-247(TC=85°C)			
Non repetitive surge peak on-state current	I _{TSM}	550	A
Average on-state current (180° conduction angle)	I _{T(AV)}	350	A
I ² t value for fusing (tp=10ms)	I ² t	1500	A ² S
Critical rate of rise of on-state current (I=2×IGT, tr ≤ 100 ns)	di/dt	150	A/μS
Peak gate current	I _{GM}	5	A
Average gate power dissipation	P _{G(AV)}	2	W

Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	TO-3P	0.65
		TO-247	0.60
			°C/W

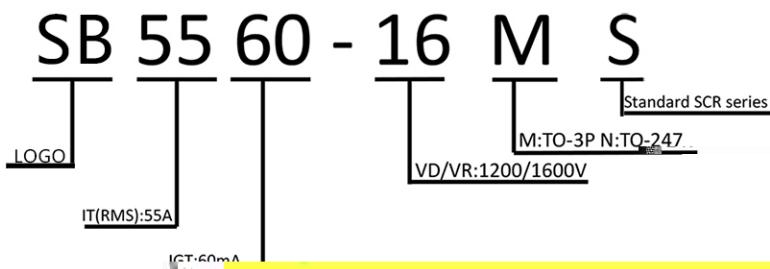
ELECTRICAL CHARACTERISTICS at $T_j = 25^\circ\text{C}$ unless otherwise specified

Symbol	Test Condition	Value	Unit
I_{GT}	$V = 12\text{V} R = 140\Omega$	MAX.	mA
V_{GS}		MAX.	V
V_{GD}	$VD=VDRM T_j=125^\circ\text{C}$	MIN.	V
I_L	$I_G = 1.2I_{GT}$	MAX.	mA
I_H	$IT=50\text{mA}$	MAX.	mA
dV/dt	$VD=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$	MIN.	V/ μs

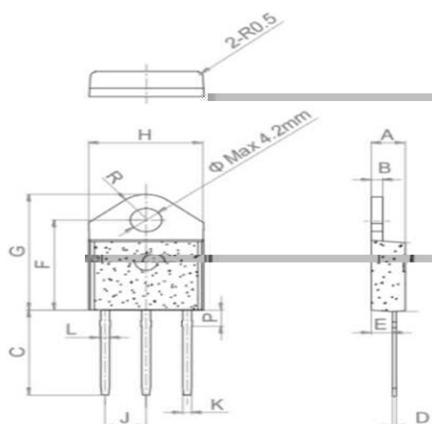
STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit
V_{TM}	$ITM=20A \pm 20\%$	$T_j = -25^\circ\text{C}$	A
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j = 25^\circ\text{C}$	μA
I_{RRM}		$T_j = 125^\circ\text{C}$	mA

Ordering Information Scheme

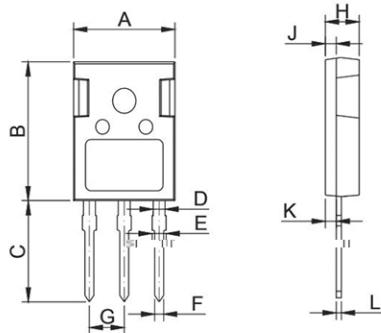


TO-3P Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.40		1.60	0.055		0.062
C	15.48		15.88	0.609		0.625
D	0.50		0.70	0.019		0.027
E	2.70		2.90	0.106		0.114
F	15.92		16.32	0.626		0.642
G	20.22		20.67	0.798		0.812
H	15.15		15.35	0.590		0.604
J		5.45			0.214	0.216
K	1.10		1.30	0.043		0.051
L	1.15		1.35	0.045		0.053
P	2.68		3.08	0.105		0.121
R		4.20			0.165	

TO-247 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	15.90	0.610	0.622	0.634
B	20.80	21.00	22.20	0.810	0.822	0.834
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.00	0.071	0.070	0.071
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.44			0.214	0.214	0.214
H	4.50 ^a	5.00 ^b	5.20 ^c	0.180	0.193	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus on-state current

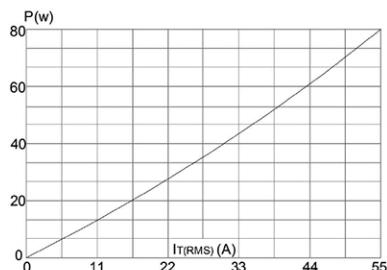


FIG.3: Surge peak on-state current versus number of cycles

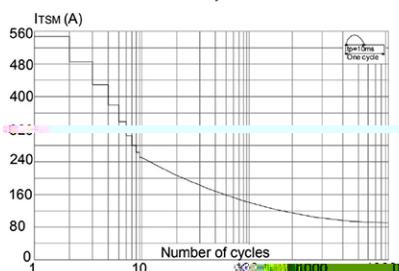


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I_2\text{ t}$

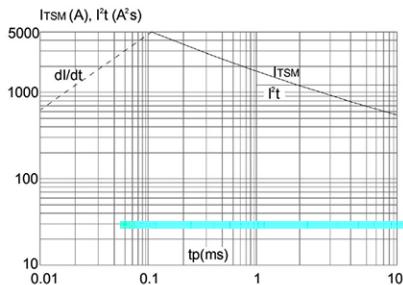


FIG.2: on-state current versus case temperature

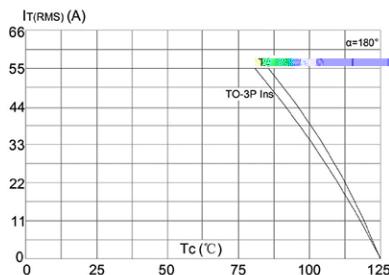


FIG.4: On-state characteristics (maximum values)

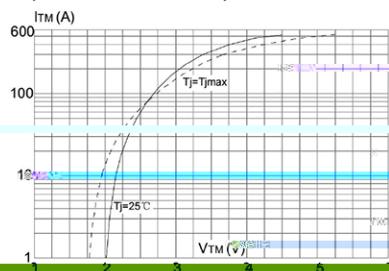


FIG.6: Relative variations of gate tridiode current, drain current, drain-to-source voltage and latching current versus junction temperature

